

Part No. ▾ FP2189-G




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FP2189-G датащи (PDF) - WJ Communication. Inc.

номер детали	FP2189-G
подробное описание детали	1-Watt HFET
объем файла	610.61 Kbytes
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производитель	WJCI [WJ Communication. Inc.]
домашняя страница	http://www.wj.com
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Автоматически

- Mobile Infrastructure
- CATV / DBS
- W-LAN / ISM
- RFID
- Defense / Homeland Security
- Fixed Wireless

The product is targeted for use as driver amplifiers for wireless infrastructure where high performance and high efficiency are required.

Specifications

DC Parameter	Units	Min	Typ	Max
Saturated Drain Current, I_{ds} ⁽¹⁾	mA	445	615	705
Transconductance, G_m	mS		280	
Pinch Off Voltage, V_p ⁽²⁾	V		-2.1	

RF Parameter ⁽³⁾	Units	Min	Typ	Max
Operational Bandwidth	MHz	50		4000
Test Frequency	MHz		800	
Small Signal Gain	dB		18.5	
SS Gain (50 Ω , unmatched)	dB	15		21
Maximum Stable Gain	dB		24	
Output P1dB	dBm		+30	
Output IP3 ⁽⁴⁾	dBm		+43	
Noise Figure	dB		4.5	
Drain Bias			+8V @ 250 mA	

1. I_{ds} is measured with $V_{gs} = 0$ V, $V_{ds} = 3$ V.
2. Pinch-off voltage is measured when $I_{ds} = 2.4$ mA.
3. Test conditions unless otherwise noted: T = 25 °C, $V_{ds} = 8$ V, $I_{DQ} = 250$ mA in an application circuit with $Z_L = Z_{Lopt}$, $Z_S = Z_{Sopt}$ (optimized for output power).
4. 30IP measured with two tones at an output power of +15 dBm/one separated by 1 MHz. The suppression on the largest IM3 product is used to calculate the 30IP using a 2:1 rule.

Absolute Maximum Rating

Parameter	Rating
Operating Case Temperature	-40 to +85 °C
Storage Temperature	-55 to +125 °C
DC Power	4.0 W
RF Input Power (continuous)	6 dB above Input P1dB
Drain to Gate Voltage, V_{dg}	+16 V
Junction Temperature	+220 °C

Typical Performance ⁽⁵⁾

Parameter	Units	Typical			
Frequency	MHz	915	1960	2140	2450
Gain	dB	18.7	15.6	14.4	13.0
Input Return Loss	dB	21	14.6	23	26
Output Return Loss	dB	8.3	12	11.5	9.6
Output P1dB	dBm	+30.2	+30.4	+30.6	+31.2
Output IP3 ⁽⁴⁾	dBm	+42.8	+43.5	+43.9	+45.3
Noise Figure	dB	4.5	3.4	4.5	
IS-95 Channel Power @ -45 dBc ACLR	dBm	+24.5	+23.8		
W-CDMA Ch. Power @ -45 dBc ACLR				+22.2	
Drain Voltage	V		+8		
Drain Current	mA		250		

5. Typical parameters represent performance in a tuned application circuit.

Ordering Information

Part No.	Description
FP2189-G	1 -Watt HFET (lead-free/green/RoHS-compliant SOT-89 package)
FP2189-PCB900S	870 – 960 MHz Application Circuit
FP2189-PCB1900S	1930 – 1990 MHz Application Circuit
FP2189-PCB2140S	2110 – 2170 MHz Application Circuit

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номер детали	подробное описание детали	Html View	производитель
FP31QF_06	2-Watt HFET	1 2 3 4 5 More	WJ Communication. Inc.
FP2189-RFID	1 - Watt HFET	1 2 3 4 5 More	WJ Communication. Inc.
FP1189	½-Watt HFET	1 2 3 4 5 More	WJ Communication. Inc.
SHF-0189	0.05 - 6 GHz 0.5 Watt GaAs HFET	1 2 3 4	SIRENZA MICRODEVICES
SHF-0186	0.05-12 GHz 0.5 Watt GaAs HFET	1 2 3 4	SIRENZA MICRODEVICES
SHF-0589	0.05-3 GHz 2 Watt GaAs HFET	1 2 3 4	SIRENZA MICRODEVICES
SHF-0289	0.05 - 6 GHz 1.0 Watt GaAs HFET	1 2 3 4	SIRENZA MICRODEVICES

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